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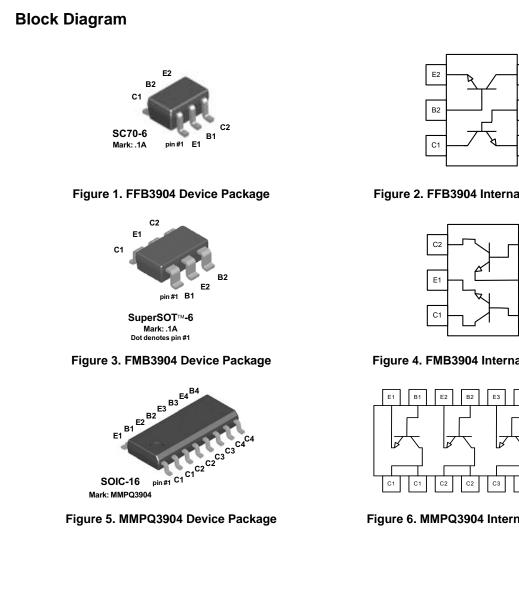


ON Semiconductor[®]

FFB3904 / FMB3904 / MMPQ3904 **NPN Multi-Chip General Purpose Amplifier**

Description

This device is designed as a general-purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier. Sourced from Process 23.



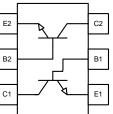


Figure 2. FFB3904 Internal Connection

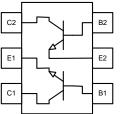
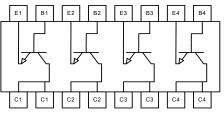
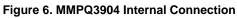


Figure 4. FMB3904 Internal Connection





Ordering Information

Part Number	Top Mark	Package	Packing Method
FFB3904	.1A	SC70 6L	Tape and Reel
FMB3904	.1A	SSOT 6L	Tape and Reel
MMPQ3904	MMPQ3904	SOIC 16L	Tape and Reel

Absolute Maximum Ratings⁽¹⁾

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ι _C	Collector Current - Continuous	200	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Note:

1. These ratings are based on a maximum junction temperature of 150°C. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics⁽²⁾

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter		Unit			
Symbol	Farameter	FFB3904	FMB3904	MMPQ3904	Onit	
PD	Total Device Dissipation	300	700	1,000	mW	
	Derate above 25°C	2.4	5.6	8.0	mW/°C	
R _{θJA}	Thermal Resistance, Junction to Ambient	415	180			
	Thermal Resistance, Junction to Ambient, Effective 4 Die			125	°C/W	
	Thermal Resistance, Junction to Ambient, Each Die			240		

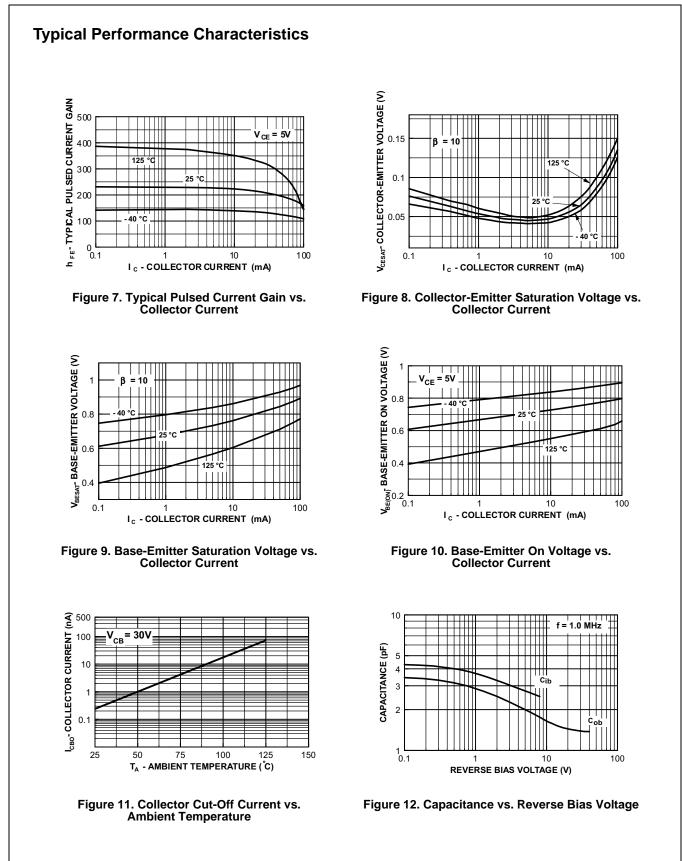
Note:

2. PCB size: FR-4 76 x 114 x 0.6T mm³ (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

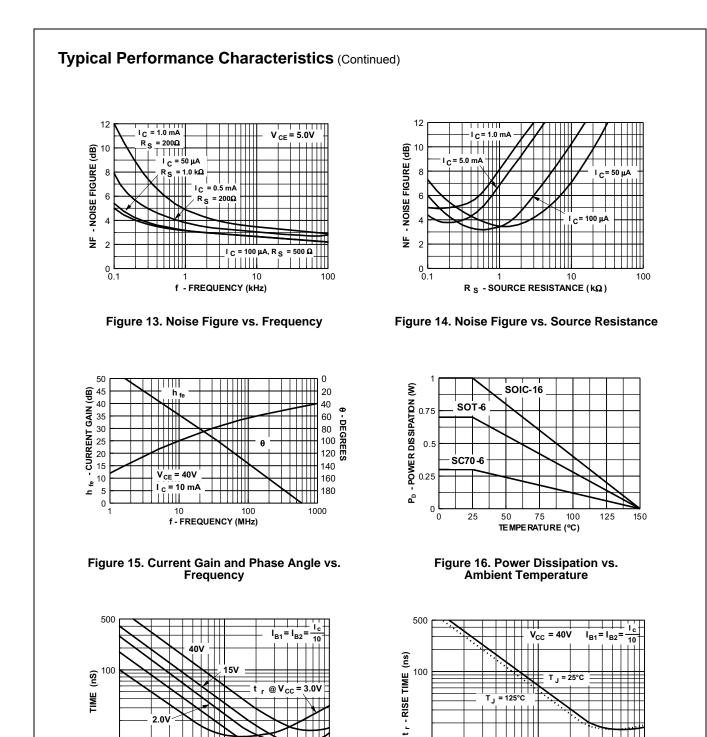
Symbol	at T _A = 25°C unless otherwise noted. Parameter		Conditions	Min.	Тур.	Max.	Unit
Off Charac			oonanono		., b.	maxi	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage		I _C = 1.0 mA, I _B = 0	40			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage		I _C = 10 μA, I _E = 0	60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage		$I_{\rm F} = 10 \mu \text{A}, I_{\rm C} = 0$	6.0			V
I _{BL}	Base Cut-Off Current		V _{CE} = 30 V, V _{BE} = -3 V			50	nA
I _{CEX}	Collector Cut-Off Current		V _{CE} = 30 V, V _{BE} = -3 V			50	nA
	teristics ⁽³⁾		01 51				
h _{FE}	FFB3904, FMB3904			40			
	DC Current Gain	MMPQ3904	I _C = 0.1 mA, V _{CE} = 1.0 V	30			
		FFB3904, FMB3904	I _C = 1.0 mA, V _{CE} = 1.0 V	70			
		MMPQ3904		50			
		FFB3904, FMB3904	I _C = 10 mA, V _{CE} = 1.0 V	100		300	
		MMPQ3904		75			
		All Devices	I _C = 50 mA, V _{CE} = 1.0 V	60			
		All Devices	I _C = 100 mA, V _{CE} = 1.0 V	30			
V _{CE} (sat)	Collector-Emitter Saturation Voltage		I _C = 10 mA, I _B = 1.0 mA			0.2	v
			I _C = 50 mA, I _B = 5.0 mA			0.3	
V _{BE} (sat)	Base-Emitter Saturation Voltage		I _C = 10 mA, I _B = 1.0 mA	0.65		0.85	V
			I _C = 50 mA, I _B = 5.0 mA			0.95	
Small-Sigr	nal Characteristics	s (MMPQ3904 only)					
f _T	Current Gain-Bandwidth Product		I _C = 10 mA, V _{CE} = 20 V, f = 100 MHz		250		MHz
C _{ob}	Output Capacitance		V _{CB} = 5.0 V, I _E = 0, f = 140 kHz		4.0		pF
C _{ib}	Input Capacitance		V _{BE} = 0.5 V, I _C = 0, f = 140 kHz		8.0		pF

Note:

3. Pulse test: pulse width \leq 300 µs, duty cycle \leq 2.0%.



FFB3904 / FMB3904 / MMPQ3904 — NPN Multi-Chip General Purpose Amplifier





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t _d @ V_{CB} = 0V

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10 - COLLECTOR CURRENT (mA)

Figure 17. Turn-On Time vs. Collector Current

ТJ

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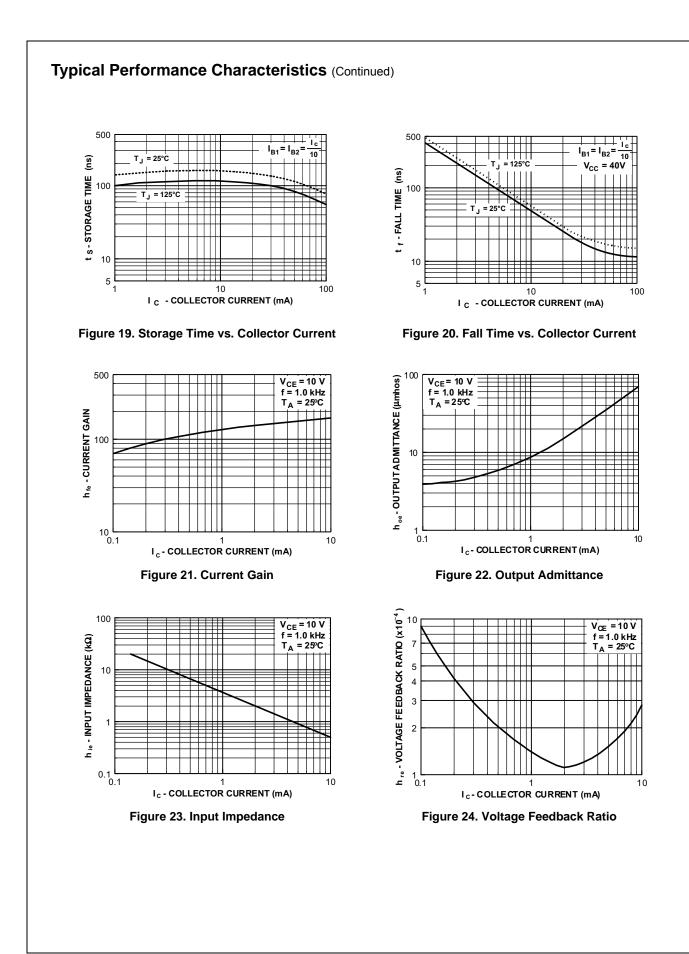
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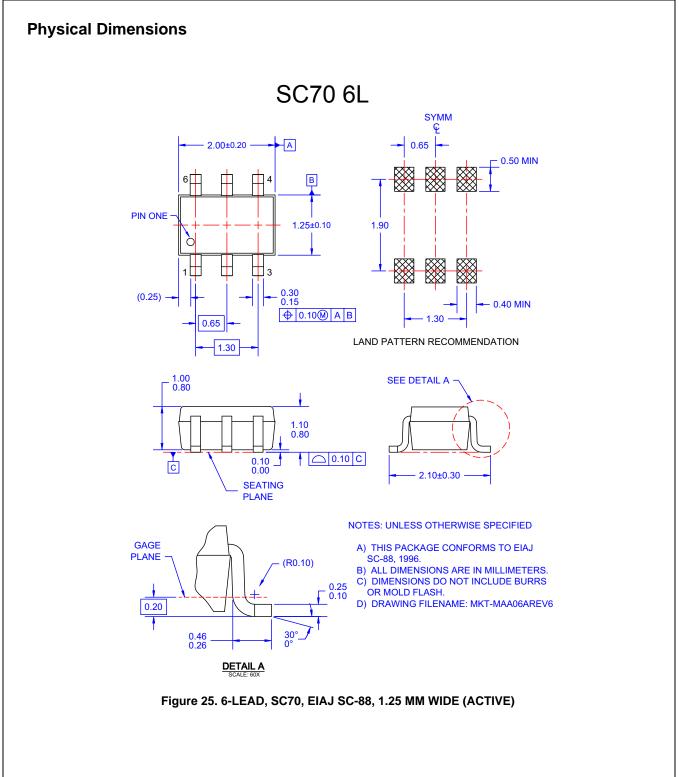
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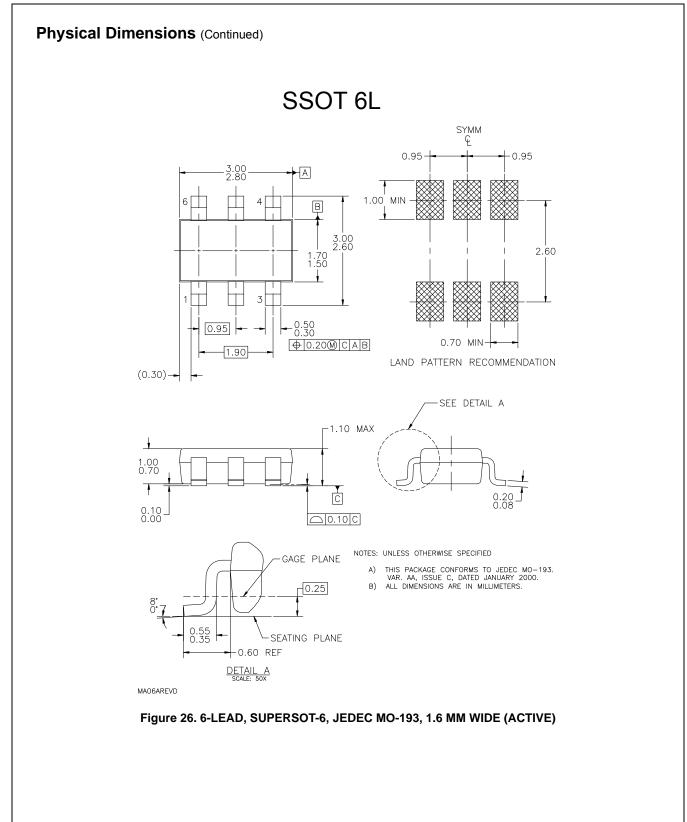
10 - COLLECTOR CURRENT (mA)

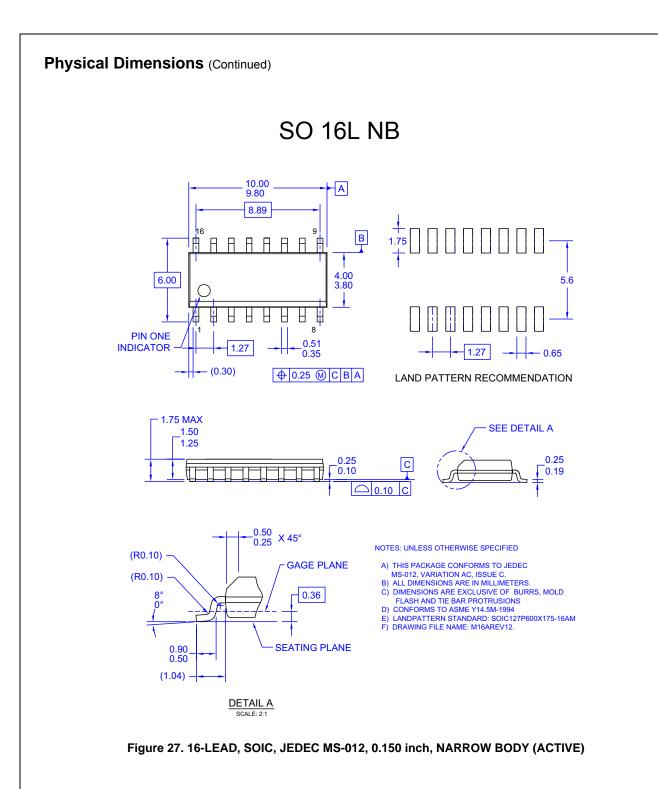
Figure 18. Rise Time vs. Collector Current

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